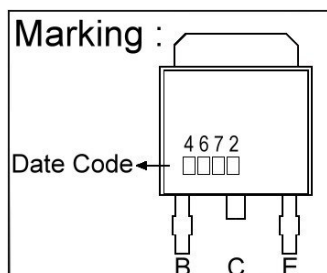
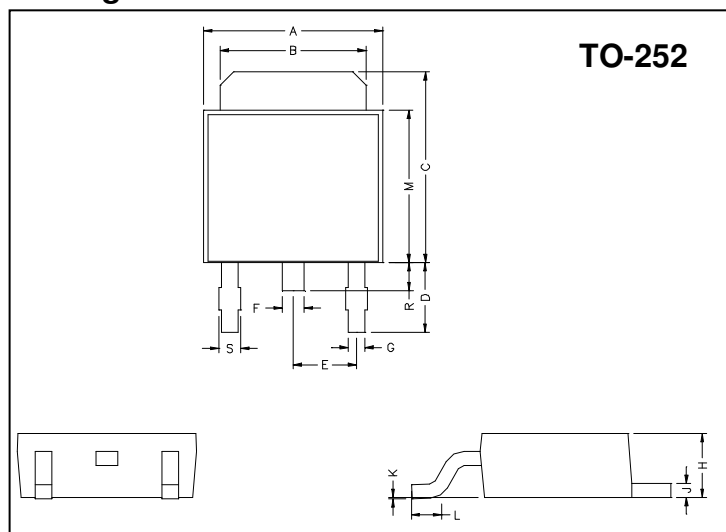


GJ4672**NPN EPITAXIAL SILICON TRANSISTOR****Description**

The GJ4672 is designed for low frequency amplifier applications.

Features

- Low saturation voltage, typically $V_{CE(sat)} = 0.1V$ at $I_C/I_B = 1A/50mA$
- Excellent DC current gain characteristics

Package Dimensions

| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 6.40 | 6.80 | G | 0.50 | 0.70 |
| B | 5.20 | 5.50 | H | 2.20 | 2.40 |
| C | 6.80 | 7.20 | J | 0.45 | 0.55 |
| D | 2.40 | 3.00 | K | 0 | 0.15 |
| E | 2.30 REF. | | L | 0.90 | 1.50 |
| F | 0.70 | 0.90 | M | 5.40 | 5.80 |
| S | 0.60 | 0.90 | R | 0.80 | 1.20 |

Absolute Maximum Ratings (TA=25°C)

| Parameter | Symbol | Ratings | Unit |
|------------------------------------|-----------|------------|------|
| Collector to Base Voltage | V_{CBO} | 60 | V |
| Collector to Emitter Voltage | V_{CEO} | 50 | V |
| Emitter to Base Voltage | V_{EBO} | 6 | V |
| Collector Current (DC) | I_C | 2 | A |
| Collector Current (Pulse PW=10ms) | I_C | 5 | A |
| Total Device Dissipation (TA=25°C) | P_D | 1.5 | W |
| Total Device Dissipation (TC=25°C) | P_D | 10 | W |
| Junction Temperature | T_J | 150 | °C |
| Storage Temperature | T_{stg} | -55 ~ +150 | °C |

Electrical Characteristics (TA = 25°C unless otherwise noted)

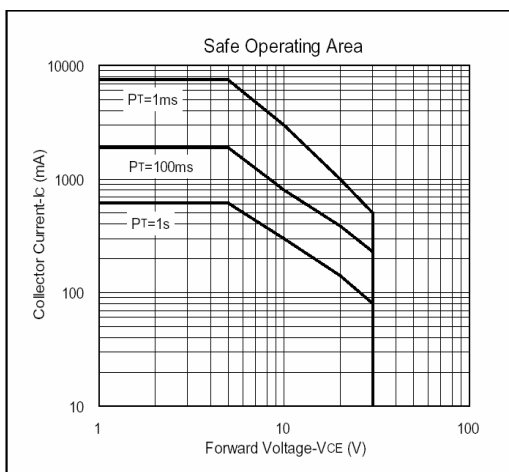
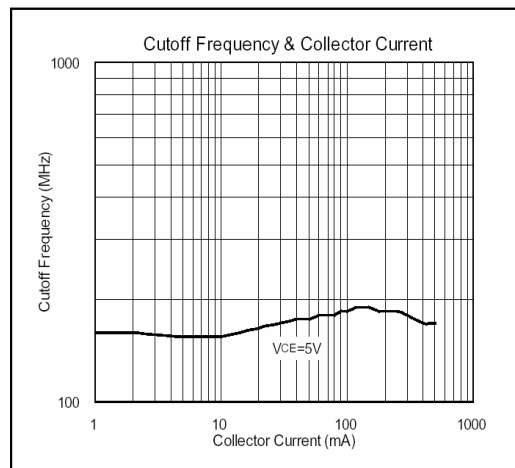
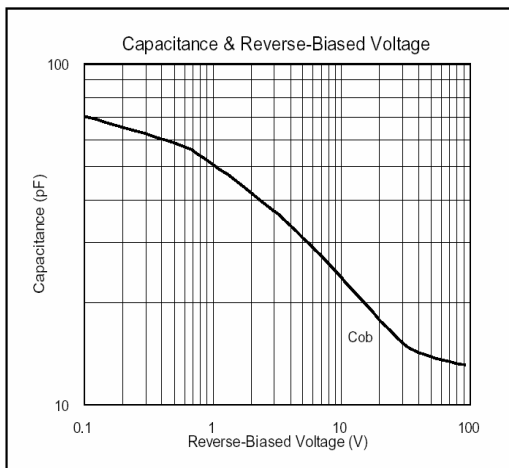
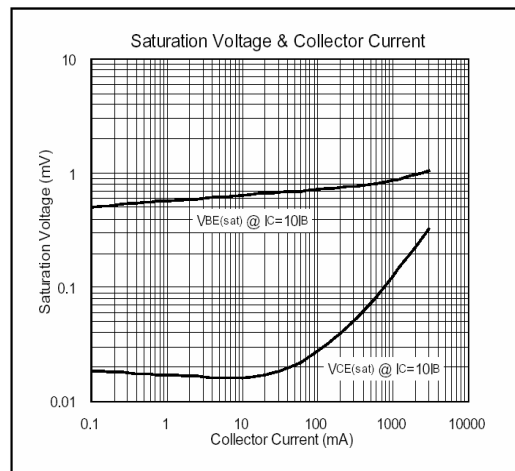
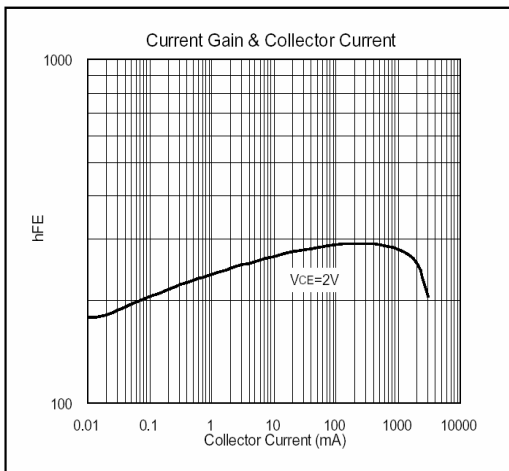
| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|-----------------|------|------|------|------|--|
| V_{CBO} | 60 | - | - | V | $I_C = 50\mu A, I_E = 0$ |
| V_{CEO} | 50 | - | - | V | $I_C = 1mA, I_B = 0$ |
| V_{EBO} | 6 | - | - | V | $I_E = 50\mu A, I_C = 0$ |
| I_{CBO} | - | - | 100 | nA | $V_{CB} = 60V, I_E = 0$ |
| I_{EBO} | - | - | 100 | nA | $V_{EB} = 5V, I_C = 0$ |
| * $V_{CE(sat)}$ | - | 0.1 | 0.35 | V | $I_C = 1A, I_B = 50mA$ |
| * h_{FE} | 120 | - | 400 | | $V_{CE} = 2V, I_C = 500mA$ |
| fT | - | 210 | - | MHz | $V_{CE} = 2V, I_E = 500mA, f = 100MHz$ |
| Cob | - | 25 | - | pF | $V_{CB} = 10V, I_E = 0, f = 1MHz$ |

*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of hFE

| Rank | A | B |
|-------|-----------|-----------|
| Range | 120 ~ 240 | 200 ~ 400 |

Characteristics Curve



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